



TS IEC 62804-1:2015

Photovoltaic (PV) Modules - Test Methods for the detection of potential-induced degradation

Part 1: Crystalline silicon
Confirmation of test results

Ref.: PVMTR-2016-40203-2

Applicant: Changzhou EGing Photovoltaic Technology Co., Ltd.
No. 18 Jinwu Road, 213213 Jintan City, China

Product: Crystalline silicon Photovoltaic (PV)-Modules

Type: A) EG-XXXM60-C-DG
B) EG-XXXP60-C-DG
C) EG-XXXM72-C-DG
D) EG-XXXP72-C-DG

XXX in the type replaces the power in watt and can be any number between:

235 – 310 for A)
235 – 295 for B)
280 – 370 for C)
280 – 355 for D)

Manufacturer: Changzhou EGing Photovoltaic Technology Co., Ltd.

Standard: TS IEC 62804-1:2015

Test conditions

Testing time: 192 h
Chamber temperature: 85°C
Relative Humidity: 85 %
Potential to ground: - 1500 V

Pass criteria

Power degradation: < 5%
Dry Insulation: > 40 MΩm²
Wet insulation: > 40 MΩm²





TS IEC 62804-1:2015

Photovoltaic (PV) Modules - Test Methods for the detection of potential-induced degradation

Part 1: Crystalline silicone
Confirmation of test results

Summary of test results:

Maximum power degradation:	required	max. 5 %
	measured	max. 1.87 %

The measured degradation is below the allowed degradation.

Dry insulation resistance:	required	24,5 M Ω for A), B) 20,5 M Ω for C), D)
	measured	>500 M Ω

The measured dry insulation resistance is above the limit.

Wet insulation resistance:	required	24,5 M Ω for A), B) 20,5 M Ω for C), D)
	measured	>500 M Ω

The measured wet insulation resistance is above the limit.

Visual inspection: No findings

The relevant bill of materials is given in Annex_1_PVMTR-2016-40203-2 and Annex_2_PVMTR-2016-40203-2.

The complete test results are given in Test Report No.: PVMTR-2016-40203-2.

VDE Prüf- und Zertifizierungsinstitut GmbH

VDE Testing and Certification Institute

Fachgebiet ET2 / Section ET2

Roland Herbert

Arnd Roth

63069 Offenbach, 2016-11-15

